

A 300GHz Wireless Transceiver in 65nm CMOS for IEEE802.15.3d Using Push-Push Subharmonic Mixer

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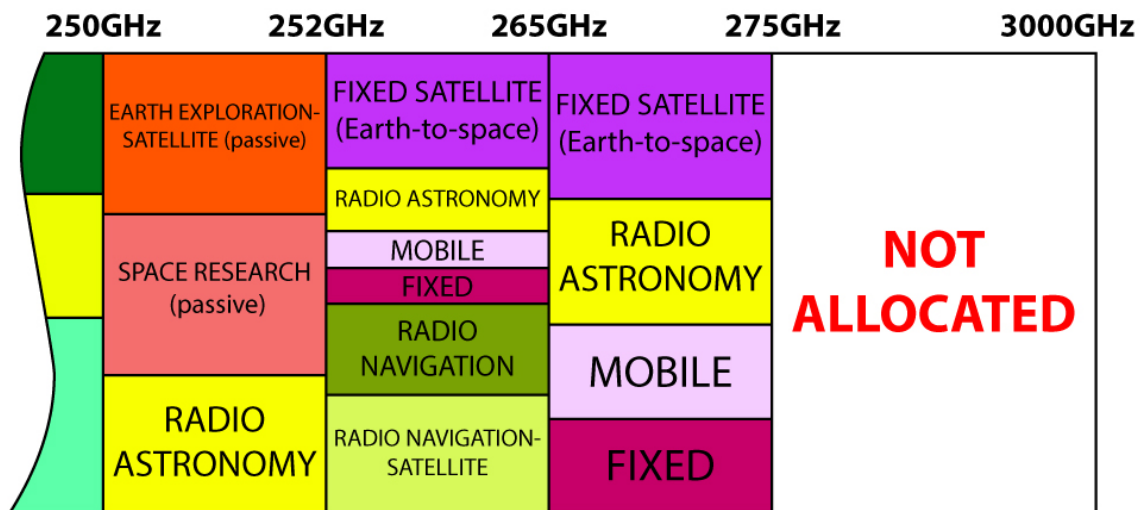
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Outline

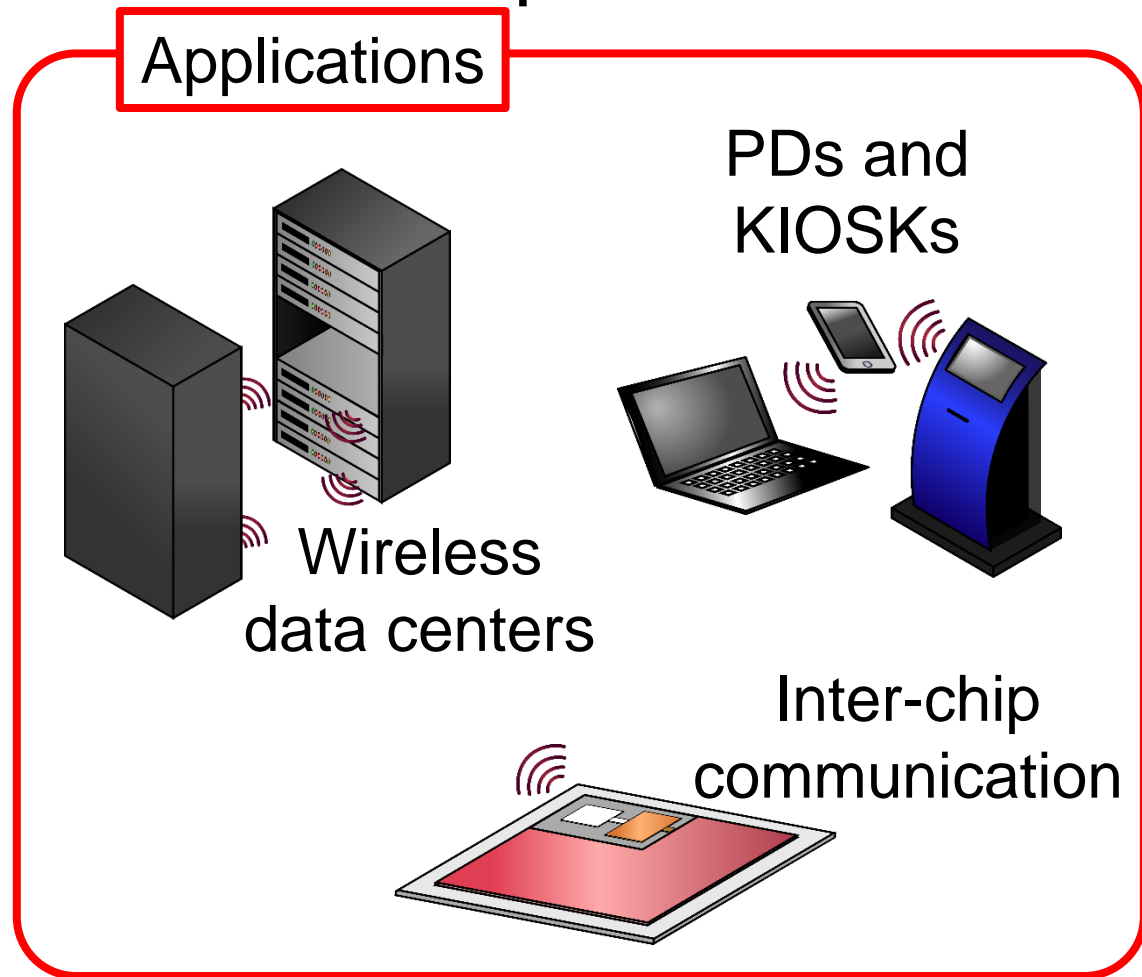
- Introduction
- Proposed 300GHz CMOS TRX
- Push-Push Subharmonic Mixer
- Fundamental Blocking Tripler
- Measurement Results
- Performance Comparison
- Conclusion

Motivation for 300GHz Communication

- Wide available bandwidth at an unallocated spectrum

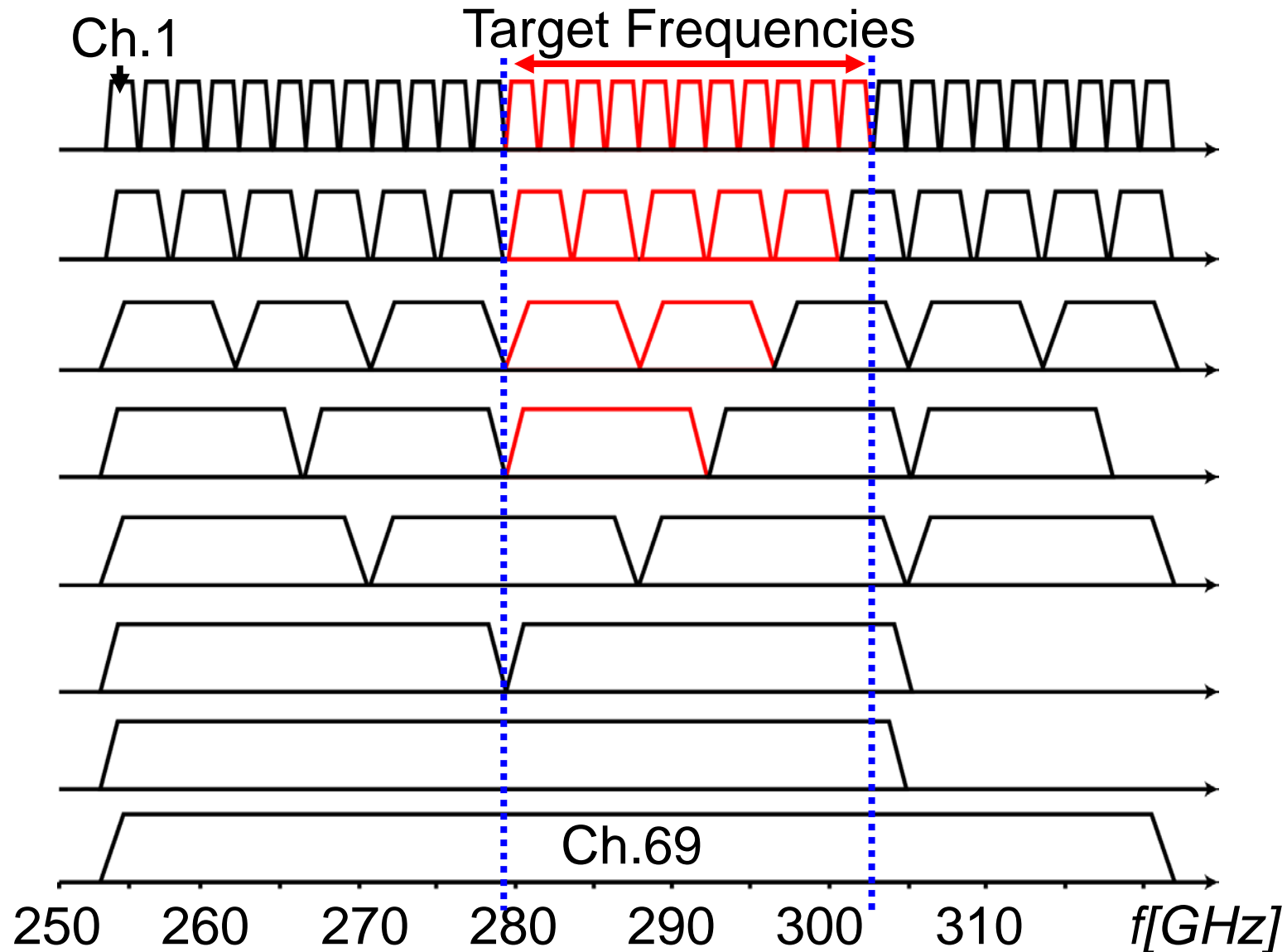


FCC Online Table of Frequency Allocations, Mar. 2020



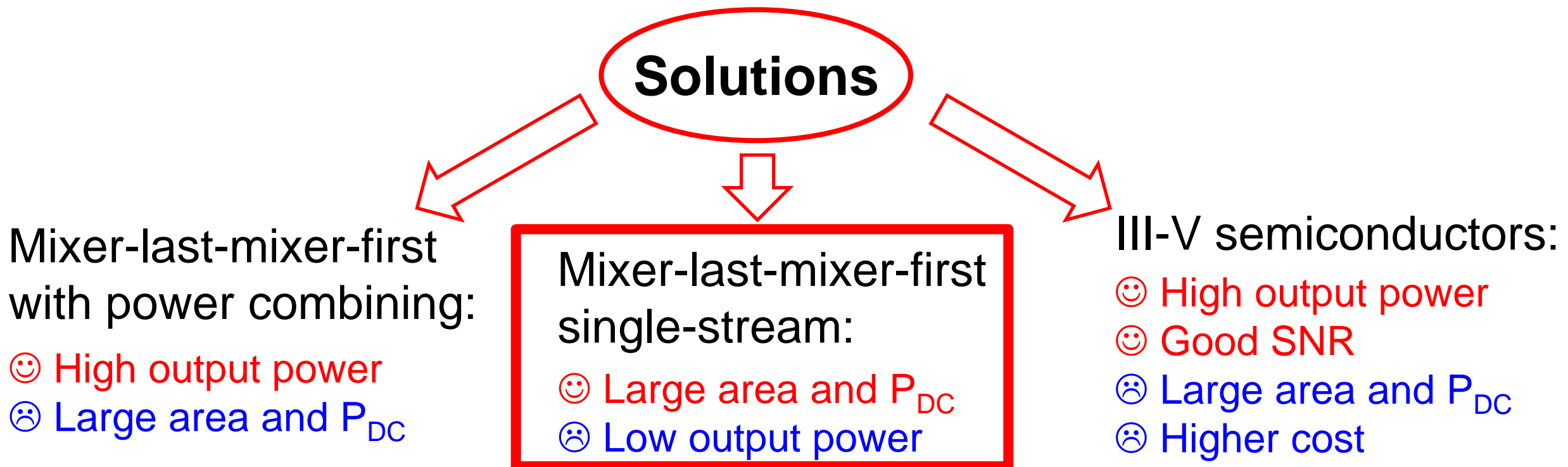
IEEE 802.15.3d

- 69 channels
- Target channels:
 - Ch.13-23 (2.16GHz)
 - Ch.39-43 (4.32GHz)
 - Ch.52-53 (8.64GHz)
 - Ch.59 (12.96GHz)

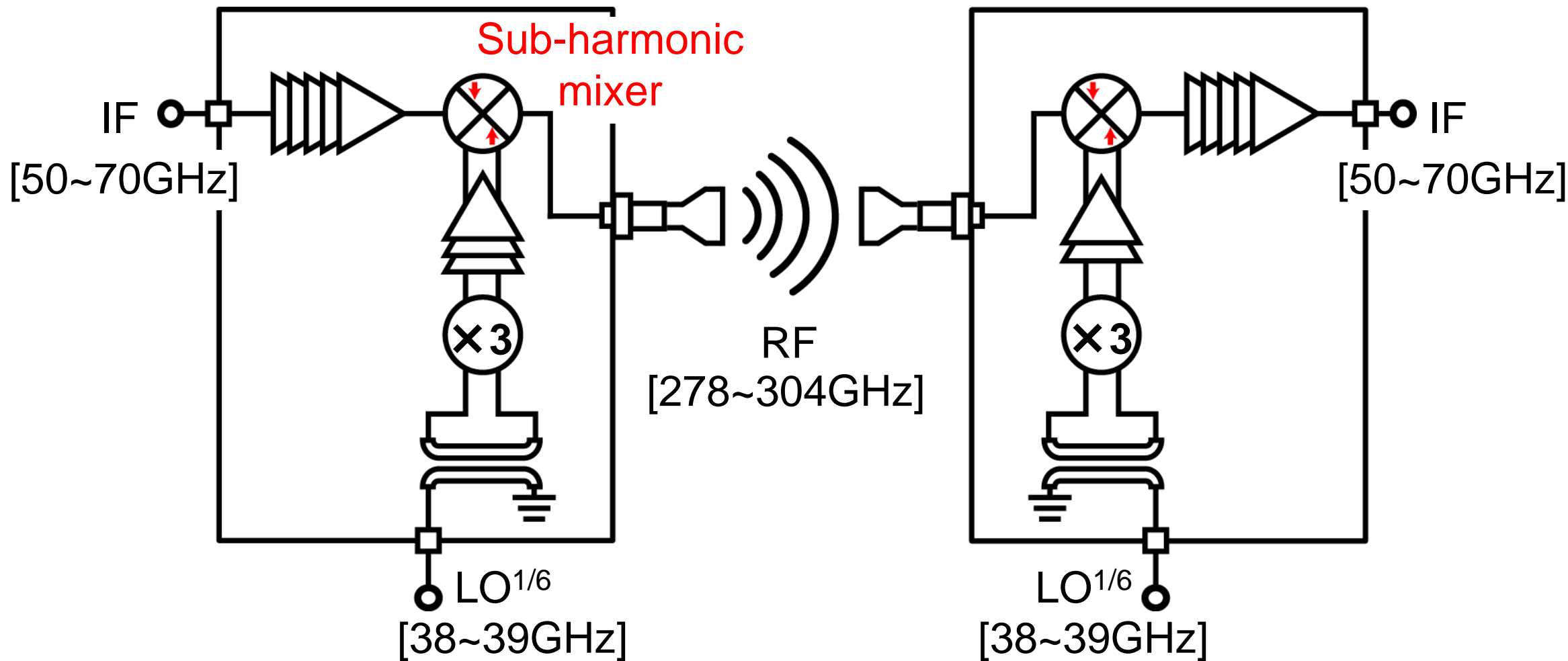


The Main Challenge

- f_{\max} of CMOS processes $< 300\text{GHz}$
 - PA and LNA are not feasible
 - Lower achievable SNR



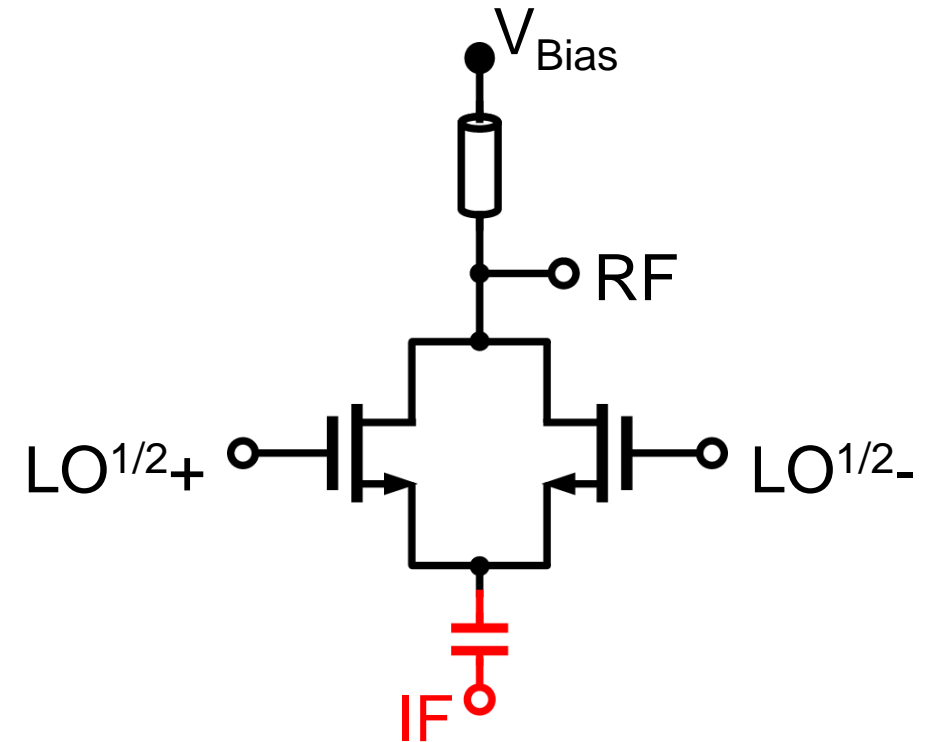
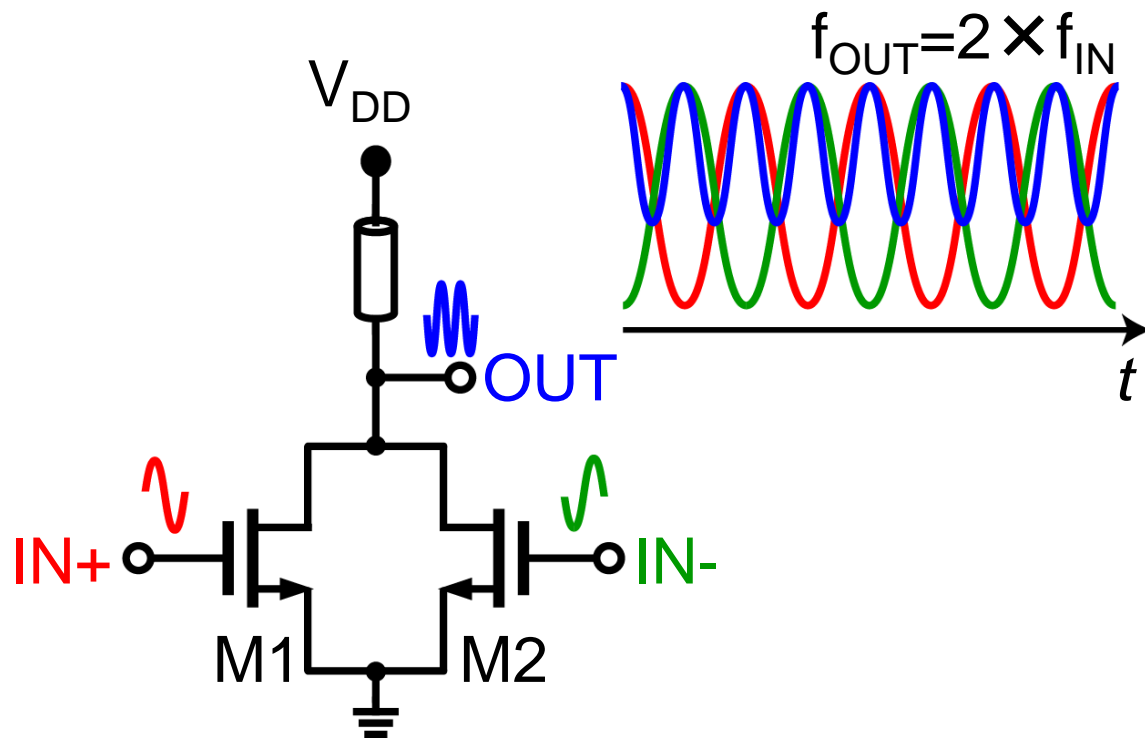
Proposed 300GHz CMOS TRX



High mixer conversion gain is required to overcome the absence of amps

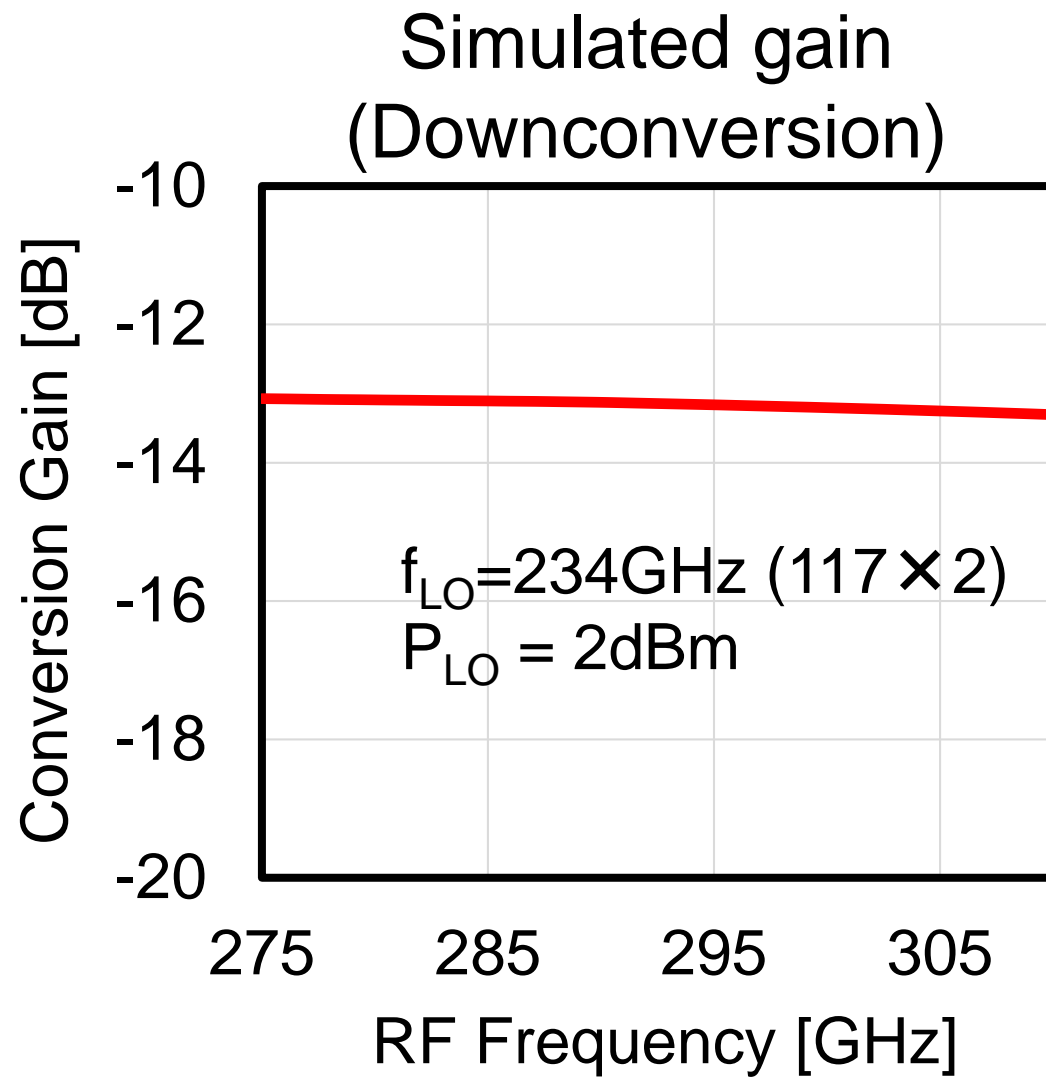
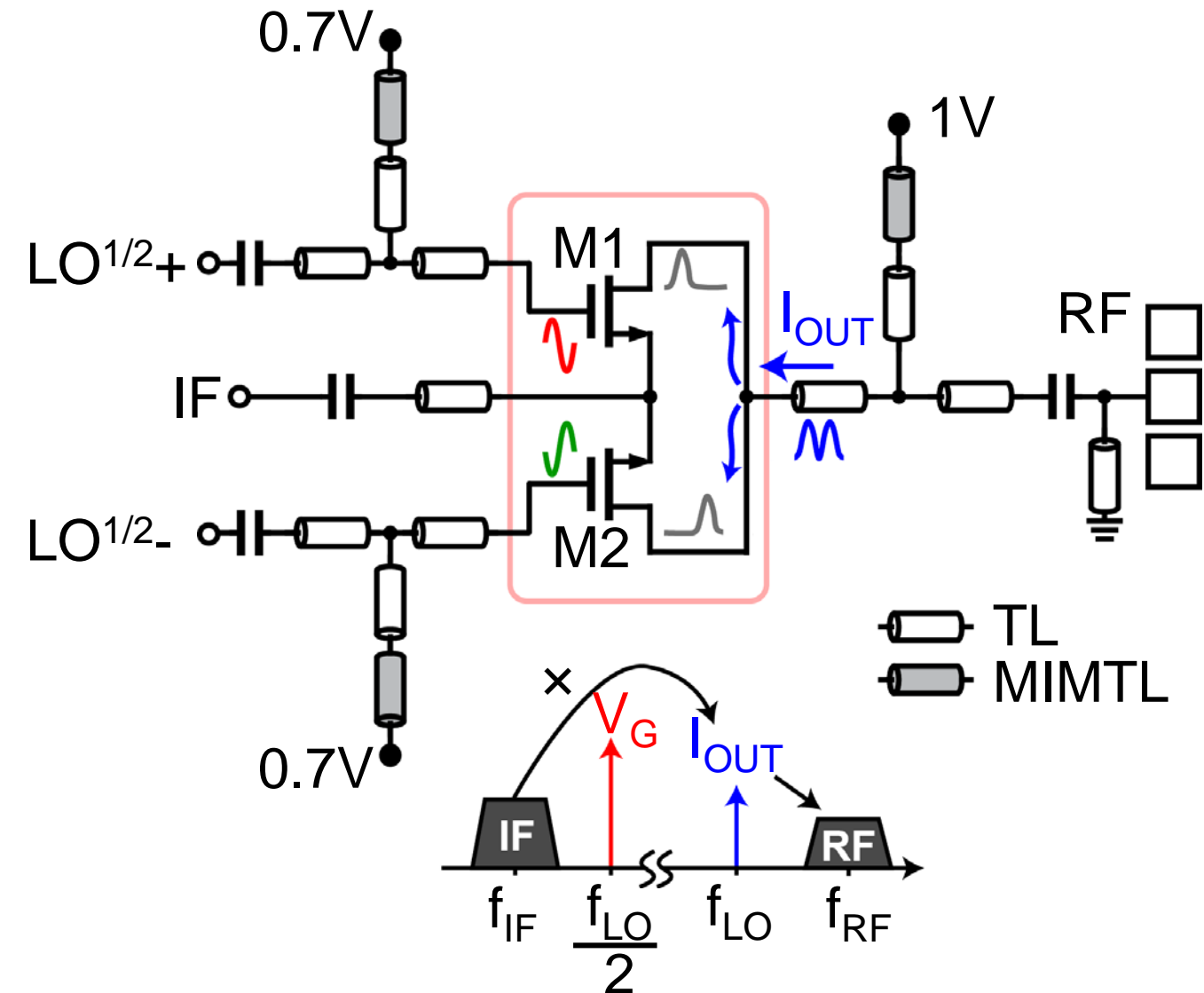
Push-Push Subharmonic Mixer

Push-push doubler



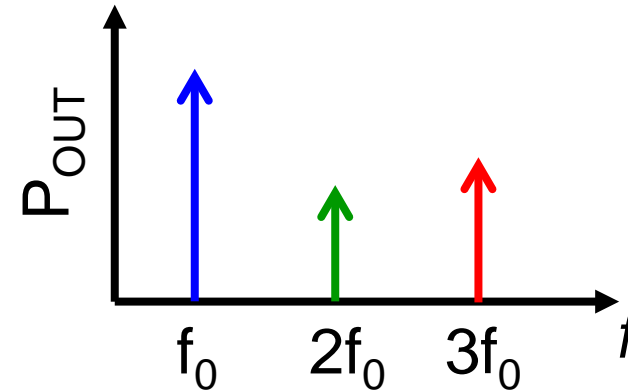
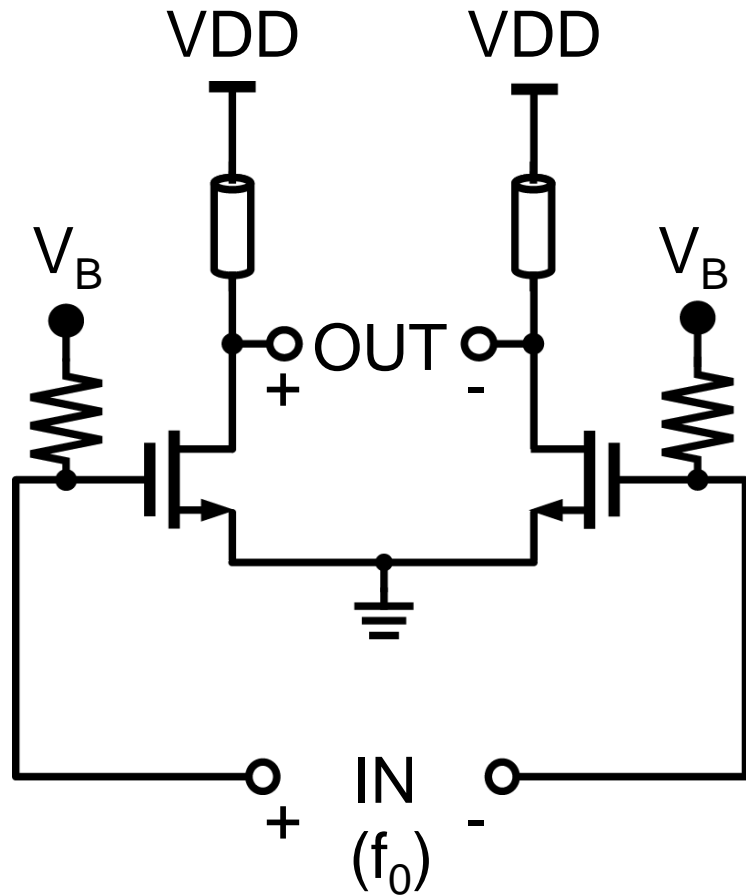
- ☺ Fundamental-like mixing
- ☺ Passive and single-ended
- ☹ High LO feedthrough

Push-Push Subharmonic Mixer



Fundamental Blocking Tripler

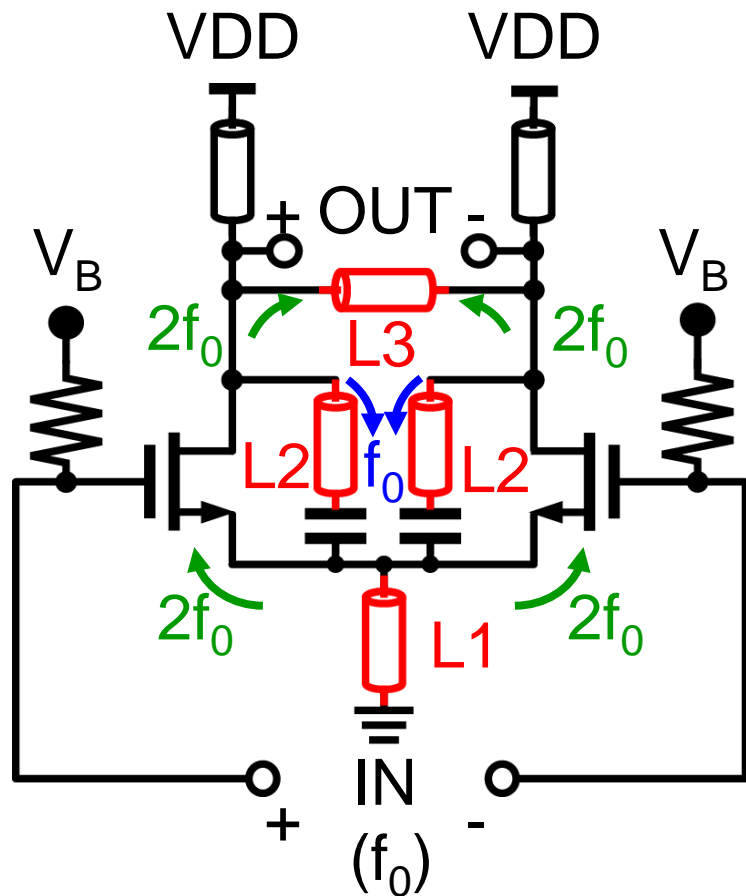
- Conventional design issues



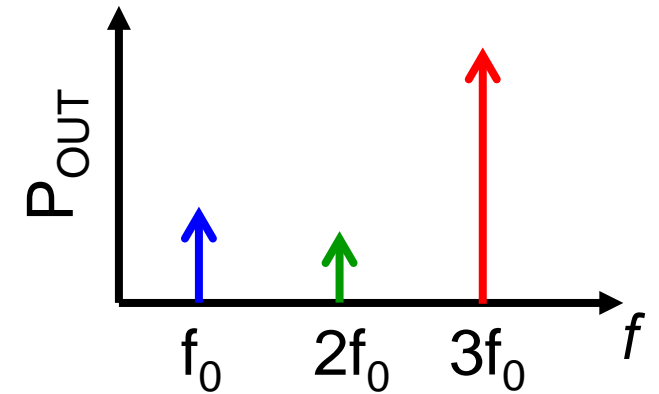
- ☹ f_0 dominates the output.
- ☹ $2f_0$ appears due to balun mismatch

Fundamental Blocking Tripler

- Proposed tripler



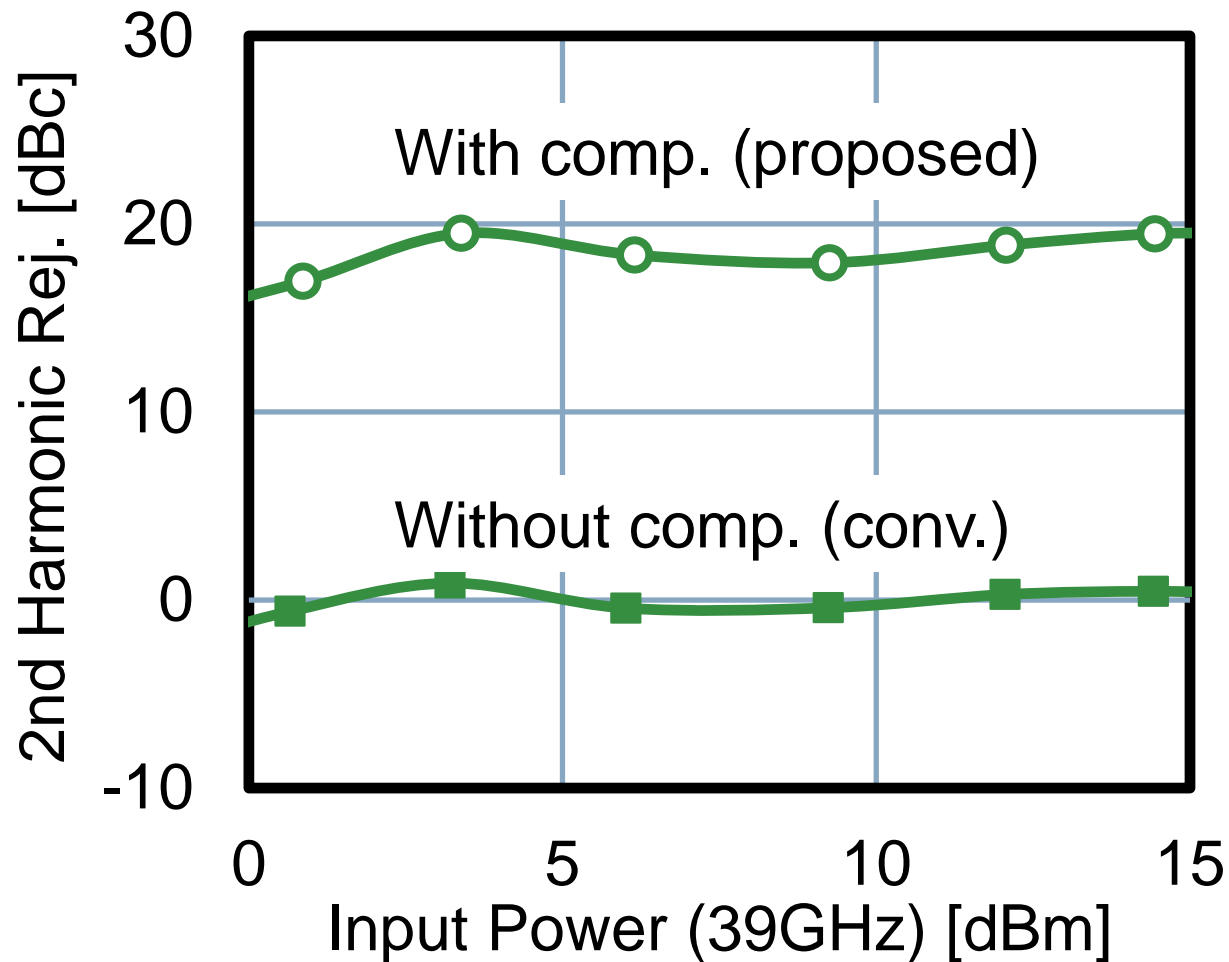
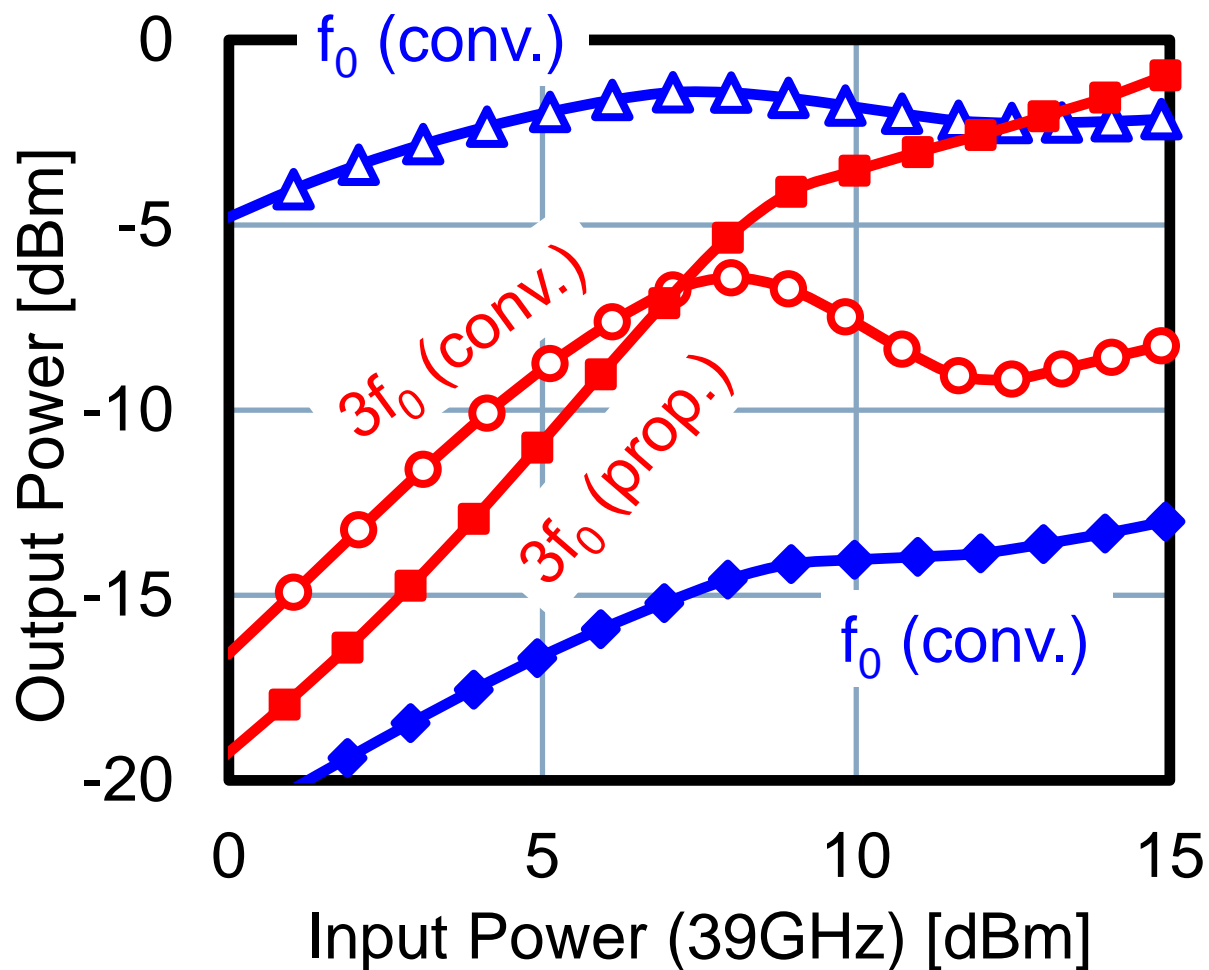
Line	Electrical length		
	@ f_0	@ $2f_0$	@ $3f_0$
L1	$\lambda/12$	$\lambda/6$	$\lambda/4$
L2	$\lambda/12$	$\lambda/6$	$\lambda/4$
L3	$\lambda/4$	$\lambda/2$	$3\lambda/4$



- ☺ f_0 cancelled or grounded.
- ☺ $2f_0$ reduced by mismatch cancellation.
- ☺ $2f_0$ reused at tail node by mixing with f_0 .
- ☺ Improved linearity.

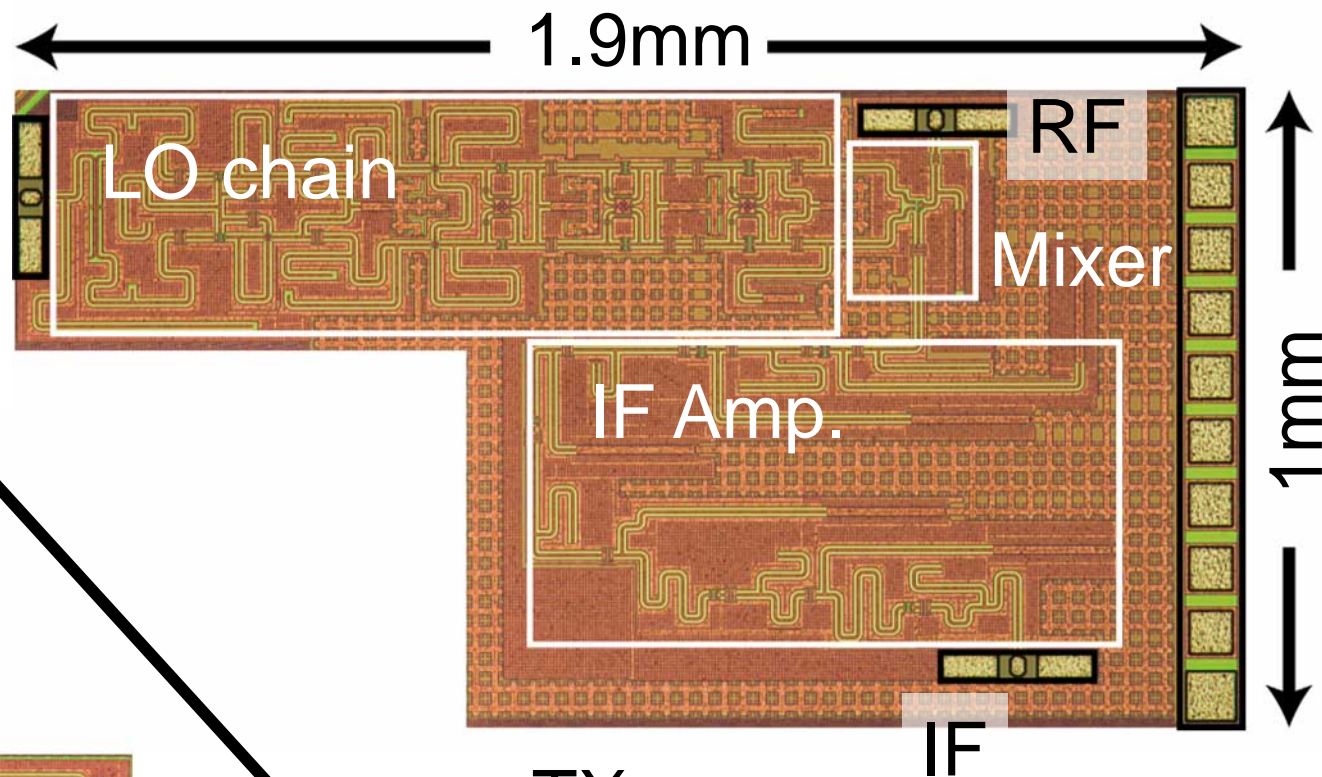
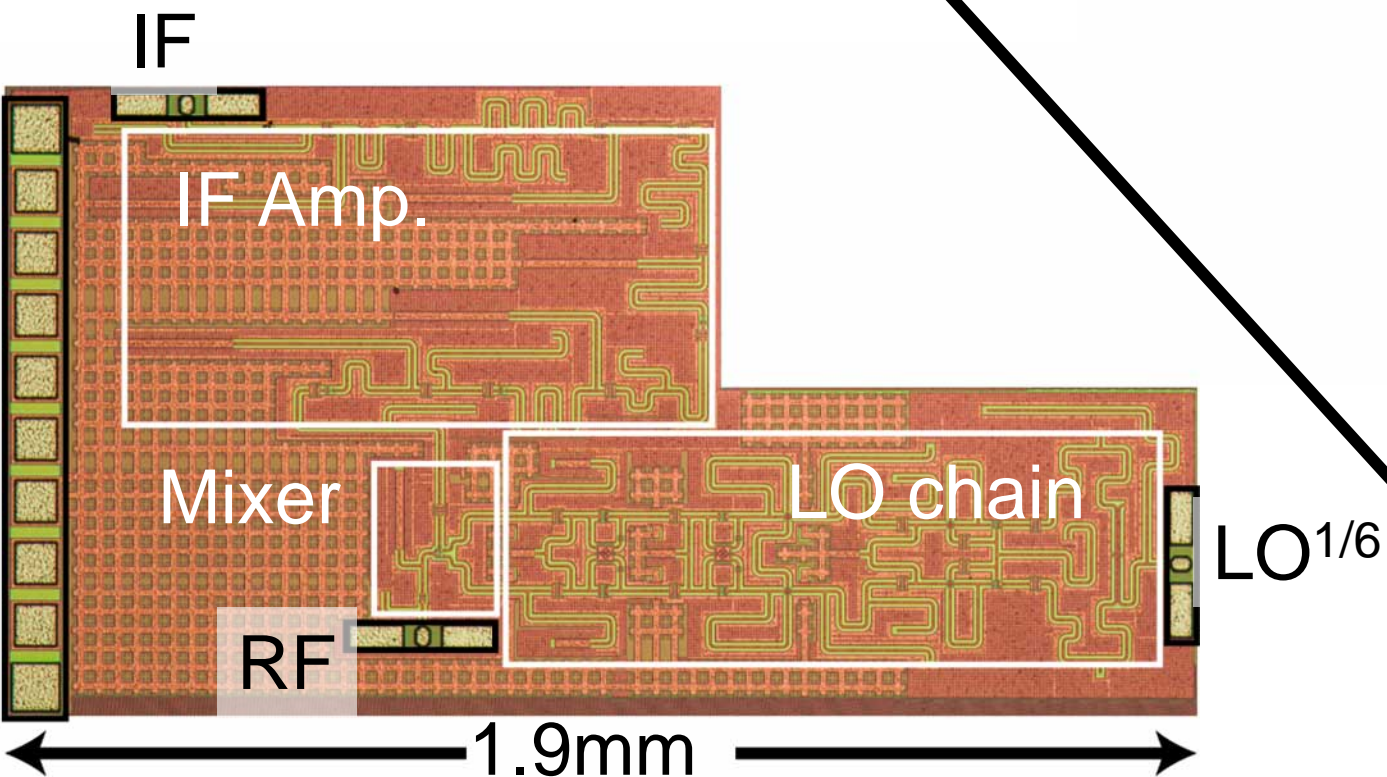
Fundamental Blocking Tripler

- Simulation Results



Chip Dimensions

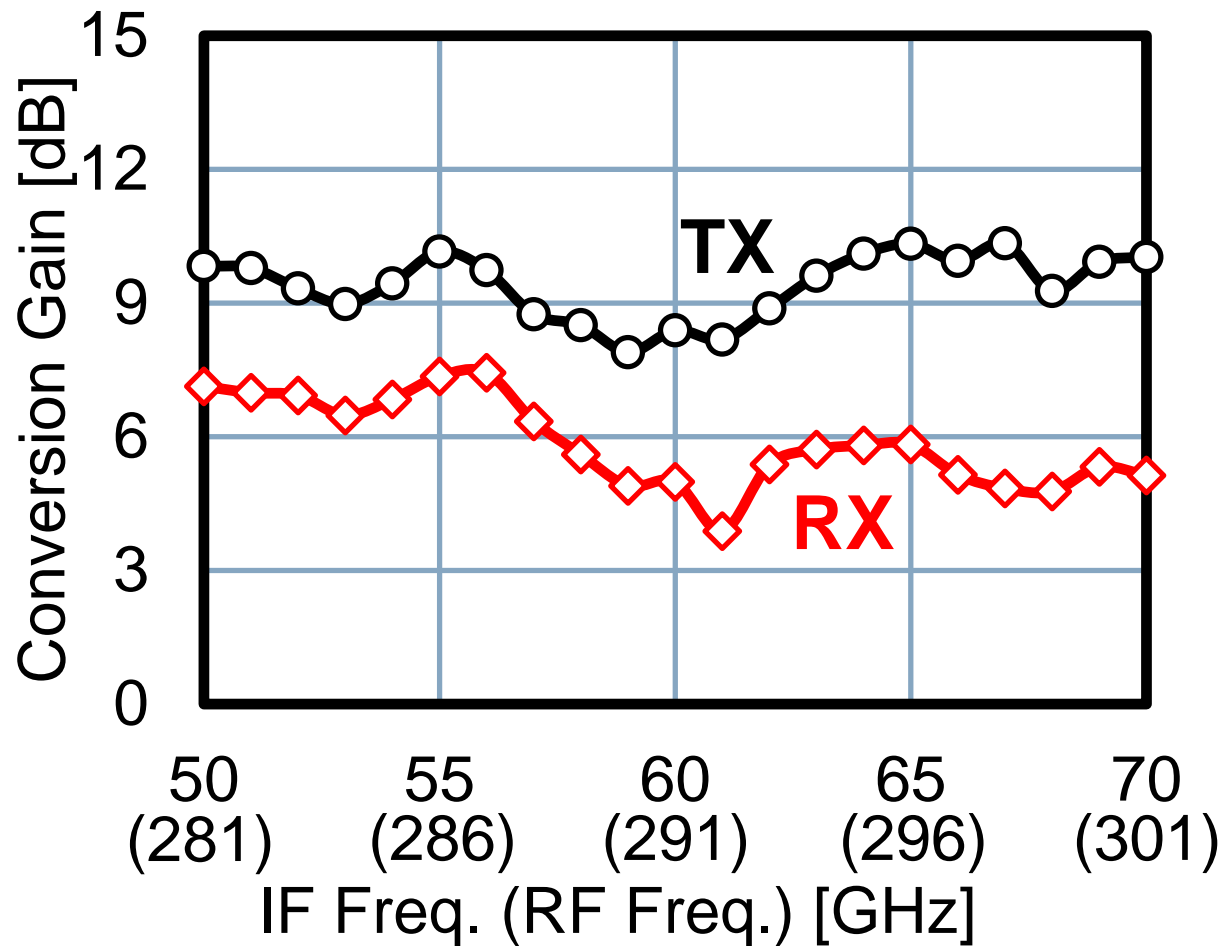
RX
Die area = 1.9mm^2
Circuit area = 1.52mm^2



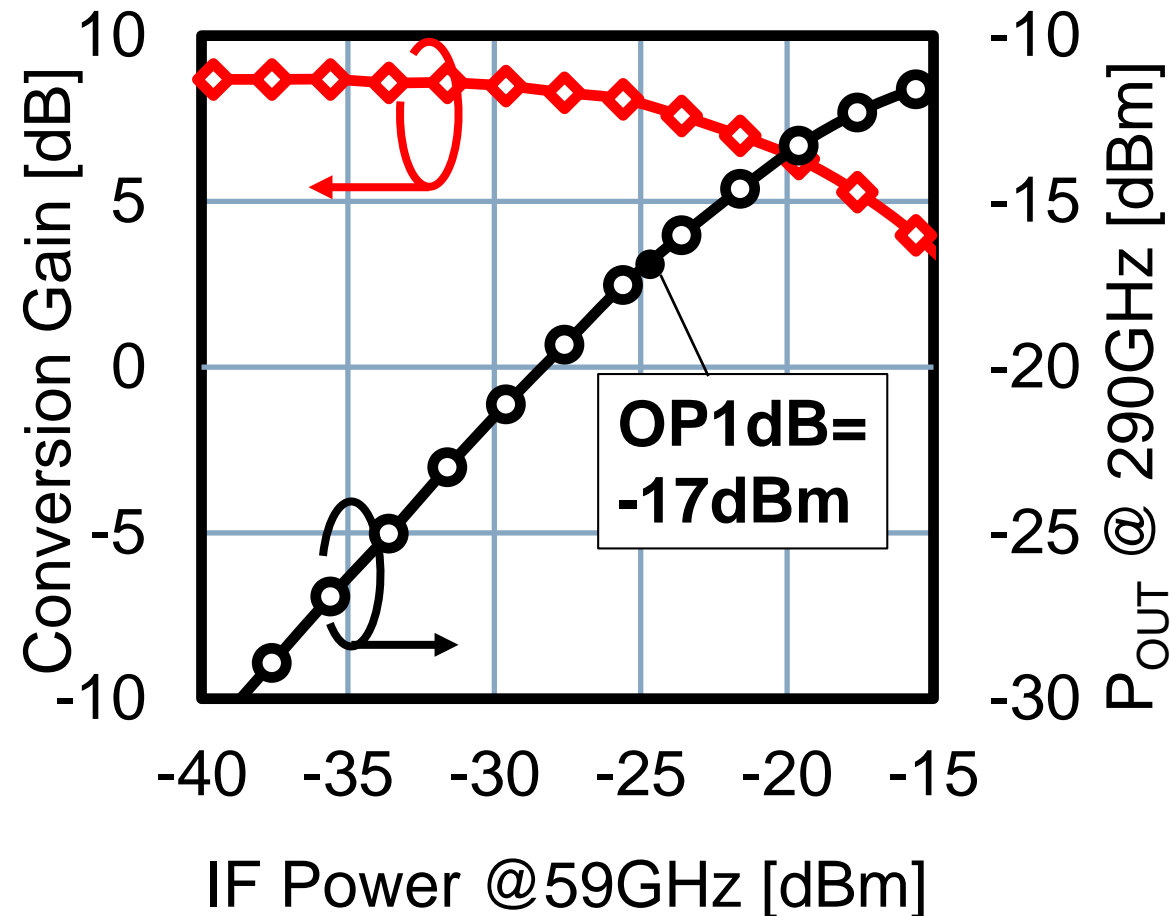
TX
Die area = 1.9mm^2
Circuit area = 1.49mm^2

Measurement Results (Characterization)

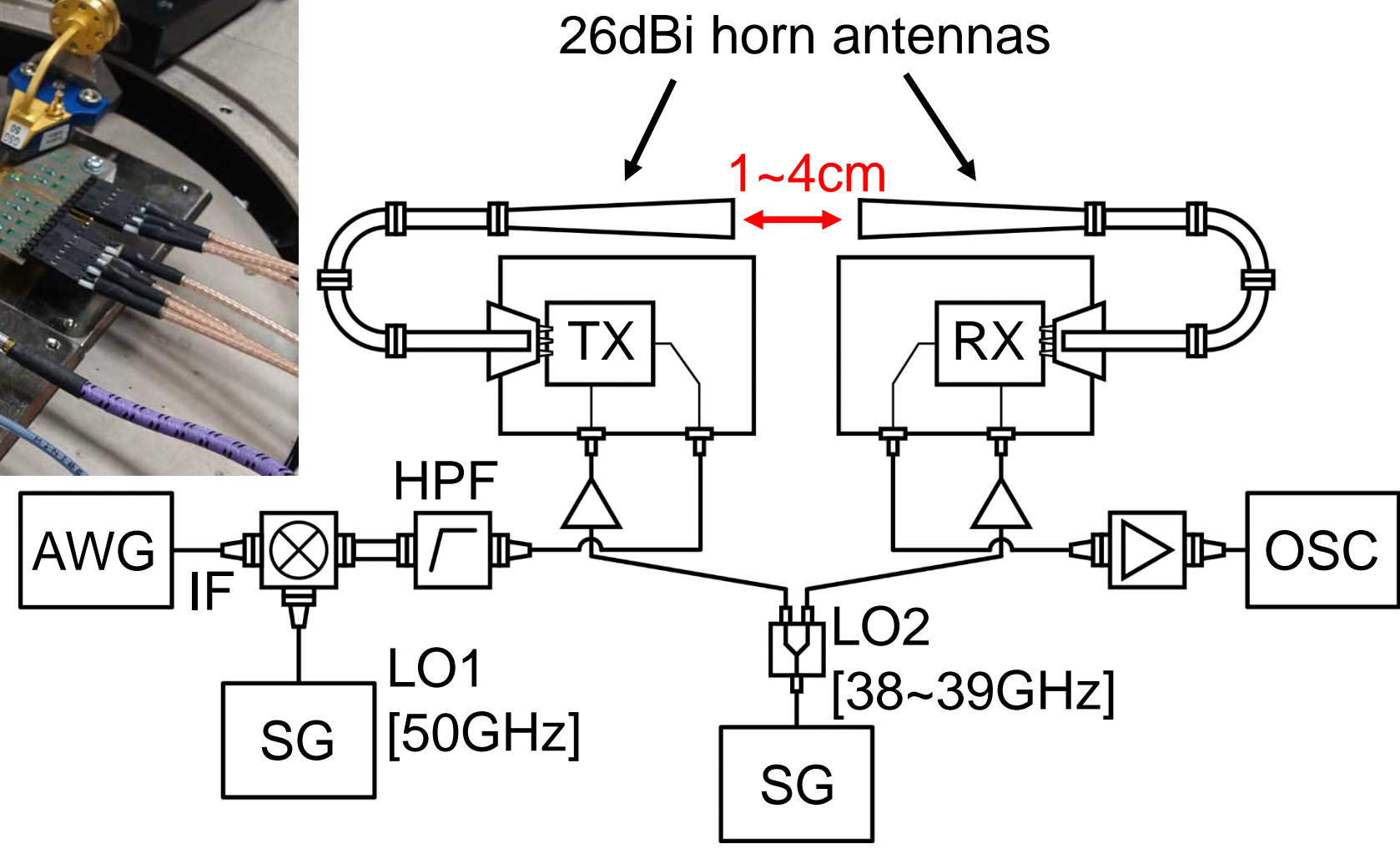
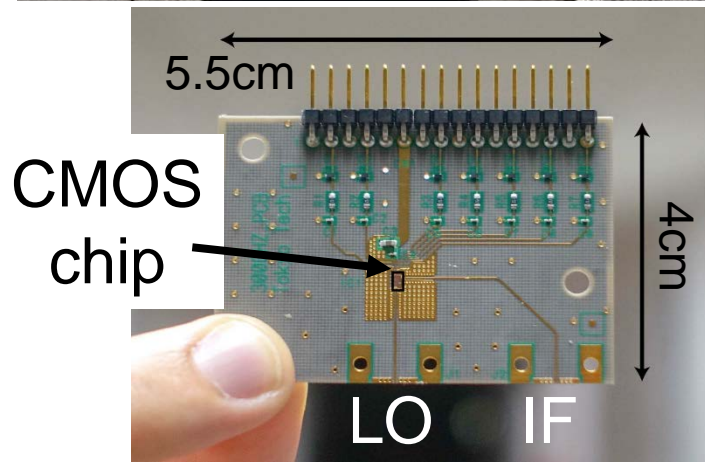
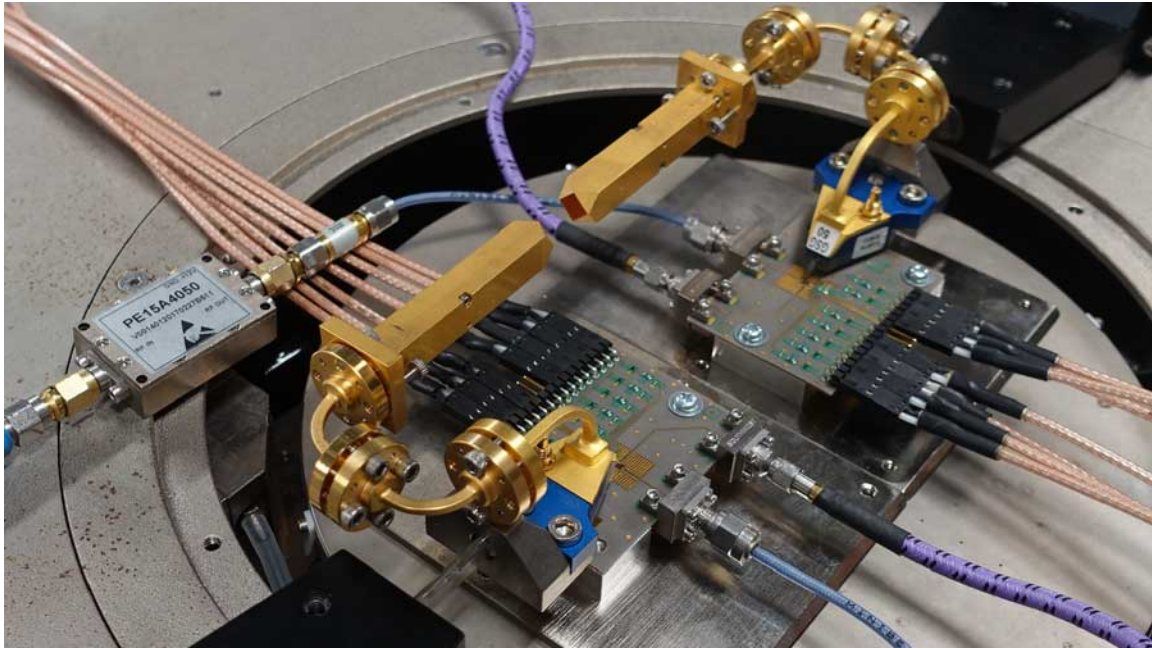
Conversion Gain @ $f_{LO}=231\text{GHz}$



TX linearity

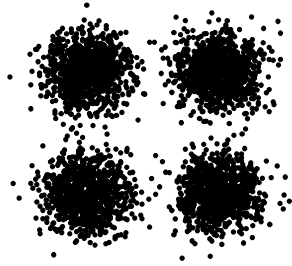
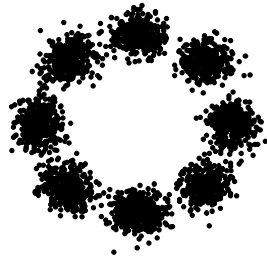
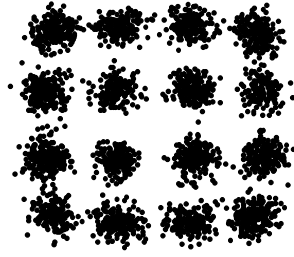


TRX Wireless Measurement Setup



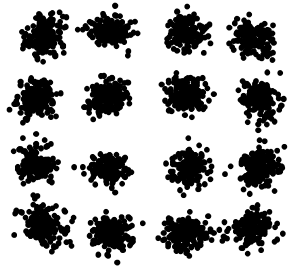
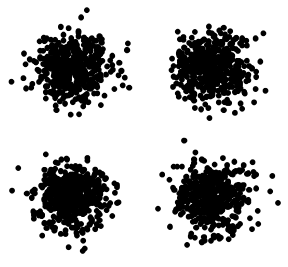
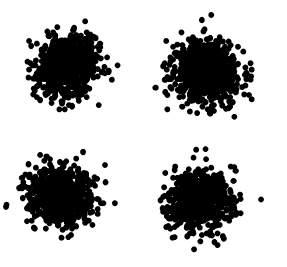
TRX Measurement Results

- Maximum data rate conditions

Distance [cm]	1		
f_{center} [GHz]	288		
f_{LO} [GHz]	228		
Bandwidth [GHz]	20.86	12.27	7.36
Symbol rate [Gbaud]	17	10	6
Modulation	QPSK	8PSK	16QAM
TX-to-RX Constellation			
TX-to-RX EVM [dB]	-10.12	-14.83	-16.72
Data rate [Gb/s]	34	30	24

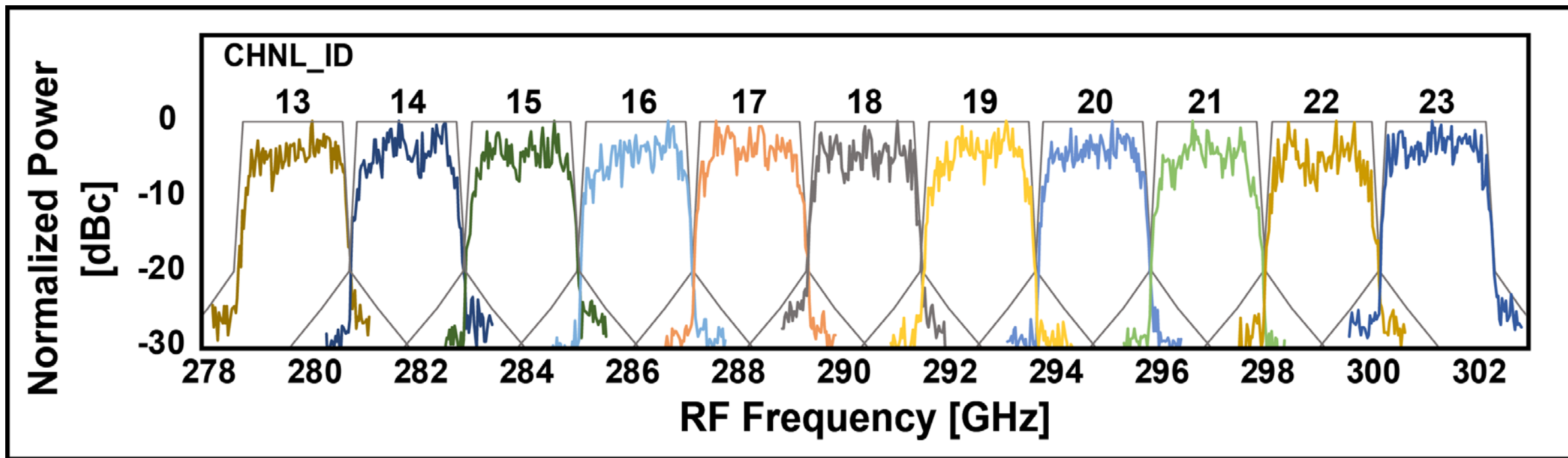
TRX Measurement Results

- IEEE802.15.3d channels:

CHNL_ID	41	43	59
f_{center} [GHz]	289.44	298.08	285.12
f_{LO} [GHz]	228	234	228
Bandwidth [GHz]	4.32	4.32	12.96
Symbol rate [Gbaud]	3.52	3.52	10.56
Modulation	16QAM	QPSK	QPSK
TX-to-RX Constellation			
TX-to-RX EVM [dB]	-17.81	-11.98	-13.04
Data rate [Gb/s]	14.08	7.04	21.12

TX Spectrum

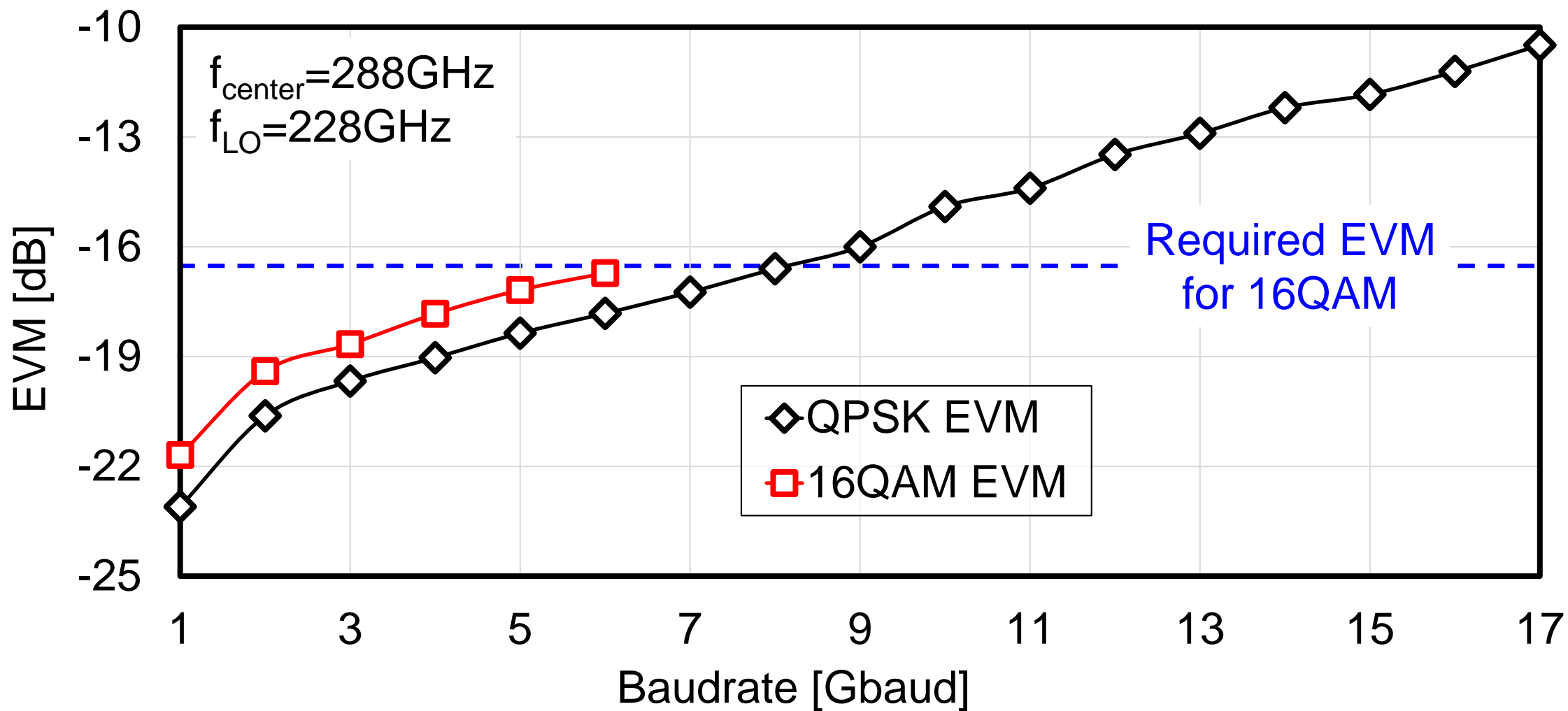
- IEEE802.15.3d Standard compatibility



*CHNL_ID is the channel ID as defined by IEEE802.15.3d standard [1] (e.g. for ch.20, CHNL_ID=20).

**Roll-off factor of all the measurements is 0.25 as specified by the standard.

EVM vs Baud Rate (1cm distance)



Performance Comparison

	[4] IHCT	[5] NTT	[6] NTT	[7],[9] UCB	[8],[10] Hiroshima	[11], [12] Hiroshima	This work
Technology [nm]	130 SiGe	80 InP- HEMT	80 InP- HEMT	65 CMOS	40 CMOS	40 CMOS	65 CMOS
RF freq. [GHz]	220-255	272-302	290*	240*	290*	252-279	278-304
Max. baud rate [Gbaud]	23.75	25	30	8	14	20	17
Max. data rate [Gb/s]	95	100	120	16	32	80	34

*Center frequency.

Performance Comparison

	[4] IHCT	[5] NTT	[6] NTT	[7],[9] UCB	[8],[10] Hiroshima	[11], [12] Hiroshima	This work
RX mixer CG [dB]	8 ^{\$}	-15	-	-	-19	-	-16.5
TX P _{sat} [dBm]	5.5	9.5	12	1	-5.5	-1.6	-11.6
Standard-based	No	No	No	No	No	IEEE 802.15.3d	IEEE 802.15.3d
P _{DC} [W]	TX: 0.96 RX: 0.45	TX: N/A RX: N/A	TX: N/A RX: N/A	TX: 0.22 RX: 0.26	TX: 1.4 RX: 0.65	TX: 0.89 RX: 0.9	TX: 0.27 RX: 0.14
Area [mm ²]	TX: N/A RX: N/A	TX: N/A RX: N/A	TX: N/A RX: N/A	TX: 2 RX: 2	TX: 5.19 RX: 3.15	TRX: 11	TX: 1.9 RX: 1.9

^{\$}Including baseband amplifier gain.

Conclusion

- A 300GHz CMOS-only TRX that achieves a maximum data rate of 34Gb/s was presented.
- A push-push sub-harmonic mixer with a conversion gain of around -16.5dB is proposed to enable single-stream operation.
- Accordingly, Power consumption and total area are reduced to less than 500mW and 4mm², respectively.
- QPSK communication is achievable for baud rates as large as 17Gbaud.

Acknowledgement

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